

ABSTRACT OF THE DISCLOSURE

A method of fabricating a semiconductor epitaxial wafer having doped carbon includes the steps of mixing
5 a quantity of carbon with a quantity of silicon and then
melting together the quantities of carbon and silicon,
growing an ingot with carbon from the melted silicon
containing carbon, grinding the ingot having carbon so
as to produce a flat surface and a notch, slicing the
10 ingot having carbon into a piece of silicon wafer,
polishing the silicon wafer having carbon, and growing
an epitaxial silicon layer on a surface of the polished
silicon wafer having carbon.

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